

**SCALABLE FLASH/NV STRUCTURES AND DEVICES
WITH EXTENDED ENDURANCE**

Abstract of the Disclosure

- 5 Devices and methods are provided with respect to a gate stack for a nonvolatile structure. According to one aspect, a gate stack is provided. One embodiment of the gate stack includes a tunnel medium, a high K charge blocking and charge storing medium, and an injector medium. The high K charge blocking and charge storing medium is disposed on the tunnel medium. The injector medium
- 10 is operably disposed with respect to the tunnel medium and the high K charge blocking and charge storing medium to provide charge transport by enhanced tunneling. According to one embodiment, the injector medium is disposed on the high K charge blocking and charge storing medium. According to one embodiment, the tunnel medium is disposed on the injector medium. Other aspects and
- 15 embodiments are provided herein.

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